Update on PXD Digitizer - SiPxlDigi

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Overview

Update on SiPxIDigi (Marlin PXD digitizer):

- New proper clustering procedure implemented (code fixes since Depfet meeting in Prague, Jan 2010)
- MCParticle "weighing" according to deposited energy implemented
- Correct fluctuations of energy loss in Si implemented (code fixes)
- Influence of ADC (Analog-To-Digital Converter) implemented, i.e. effects of "digital noise" implemented

Update on SiPxIDigi - New Clustering

- New clustering algorithm implemented each SimTrkHit is not "digitized" step-by-step into TrkHit as before, but ...
 - All hits are saved in memory
 - Based on S/NAdjacent cut (2 sigma) noise hits are generated (only in sensors, where signal(s) already is(are) - to save CPU time) Cluster seeds based on S/NSeed cut (5 sigma) are found + surroundings is searched → central part of new cluster defined For each cluster other adjacent pixels are found (based on S/NAdjacent cut) and added
 - R-Phi & Z projected positions calculated 2 algorithms implemented:
 - Cluster size <= 2 \rightarrow COG (center of gravity no etha correction)
 - Cluster size > 2 \rightarrow Analog head-tail algorithm
 - 3D position calculated, MC information + weight on each particle saved TrkHit created

Update on SiPxIDigi – Energy Loss Fluctuations

- There exist 2 different ways how to incorporate energy loss fluctuations - using Geant4 or <u>direct impl. in the digitizer</u> ...
 Geant4 particles in Si lose their energy continuously and/or produce secondary particles (preset product. thresh. cut= 80keV ~ range cut= 50µm)
 Geant4 total continuous energy loss fluctuates → described by different models, here G4UniversalFluctuations used (simple physics model of atom)
 SiPxIDigi uses the same phys. model (adapted Geant4 class for SiPxIDigi & Si material) → control of space precision /wo impact on CPU, size of data-files)
 - particles w/ βγ>=2 Energy loss fluctuations performed in SiPxIDigi (5μm step-size set)
 - particles w/ $\beta\gamma$ <2 Energy loss fluctuations performed in Geant4, deposited energy is then distributed uniformly along the path (delta-electrons, ...)
 - <u>Parameters</u>: threshold cut for secondaries = 80 keV (same as in Geant4), dE/dx|min for Si = 305 keV/mm

Update on SiPxIDigi - Corrected Energy Loss Fluctuations in Si

Studies of energy loss fluctuations in 80µm silicon - old x new ver.

- Geant4: step-size calculated automatically
- SiPxIDigi: step-size set to 5µm
- Results compared to straggling functions of Bichsel et. al . (Review of Part.
 Phys. 2009) → new version in good agreement!



500 MeV π - Energy loss fluctuations in 80 μ m silicon

Apr 16th 2010

Update on SiPxIDigi - Implementation of ADC & "Digital Noise"

ADC implementation ...

- Parameters:
 - Range: 24 000e (~ 12 μ A, gq ~ 0.5nA/e \rightarrow 24 000e), other options ~ 8 μ A, 16 μ A
 - ADC bits: 4, 6, 8 bits ADC
 - Noise range: 100e 400e
- Each pixel signal is recalculated in ADC units (1ADC ~ 24 000e/2^nBits) →
 - let's do some calculations:
 - 1 ADC for 8 bits ~ 94e
 - 1 ADC for 6 bits ~ 375e
- Clustering parameters for seeds & adjacent pixels are introduced in ADC units as well → "digital noise" introduced
 - Clustering procedure is then started

Summary & Plans

- SiP×IDigi → all we wanted is implemented !!! + well-documented !!!
 <u>Digitization</u>: Landau + Poisson fluct., drift, diffusion, deflection in mag. field
 <u>Signal process.</u>: random noise, ADC, Lorentz shift correction, clustering
- Software develop. plans:
 Corrections of simulated diffusion process → B. Schwenker is working on that → see his presentation

Backup - Simulation BelleII - Mokka

Beam pipe: cylindrical, "onion-like structure"

 inner Au layer (10 μm), inner Be layer, paraffin (active cooling), outer Be layer

 PXD: 2 layers of DEPFET detectors organized in "windmill" structure ("layer" → "ladder" → "sensor + rims")

